



**Advanced Power
Electronics Corp.**

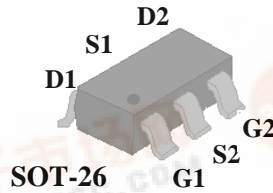
AP2530GY

Pb Free Plating Product

N AND P-CHANNEL ENHANCEMENT

MODE POWER MOSFET

- ▼ Low Gate Charge
- ▼ Low On-resistance
- ▼ Surface Mount Package
- ▼ RoHS Compliant

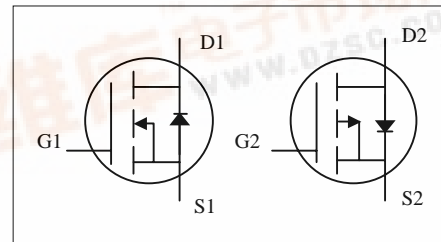


N-CH	BV_{DSS}	30V
	$R_{DS(ON)}$	72m Ω
	I_D	3.3A
P-CH	BV_{DSS}	-30V
	$R_{DS(ON)}$	150m Ω
	I_D	-2.3A

Description

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The SOT-26 package is universally used for all commercial-industrial applications.



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current ³	3.3	-2.3	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current ³	2.6	-1.8	A
I_{DM}	Pulsed Drain Current ¹	10	-10	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	1.14		W
	Linear Derating Factor	0.01		W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150		$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150		$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient ³	Max. 110	$^\circ C/W$



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N-CH Electrical Characteristics @T_j=25°C (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =1mA	-	0.02	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =3A	-	-	72	mΩ
		V _{GS} =4.5V, I _D =2A	-	-	125	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =3A	-	4	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =30V, V _{GS} =0V	-	-	1	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =24V, V _{GS} =0V	-	-	25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =3A	-	3	5	nC
Q _{gs}	Gate-Source Charge	V _{DS} =25V	-	1	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	2	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =15V	-	6	-	ns
t _r	Rise Time	I _D =1A	-	8	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =10V	-	11	-	ns
t _f	Fall Time	R _D =15Ω	-	2	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	170	270	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	50	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	35	-	pF
R _g	Gate Resistance	f=1.0MHz	-	0.5	0.8	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =0.9A, V _{GS} =0V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _S =3A, V _{GS} =0V	-	14	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	7	-	nC



P-CH Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =-1mA	-	0.03	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-2A	-	-	150	mΩ
		V _{GS} =-4.5V, I _D =-1A	-	-	280	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-3	V
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-2A	-	2	-	S
I _{DSS}	Drain-Source Leakage Current (T=25°C)	V _{DS} =-30V, V _{GS} =0V	-	-	-1	uA
	Drain-Source Leakage Current (T=70°C)	V _{DS} =-24V, V _{GS} =0V	-	-	-25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =-2A	-	3	5	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-25V	-	1	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	2	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =-15V	-	6	-	ns
t _r	Rise Time	I _D =-1A	-	8	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =-5V	-	17	-	ns
t _f	Fall Time	R _D =15Ω	-	4	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	150	240	pF
C _{oss}	Output Capacitance	V _{DS} =-25V	-	50	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	40	-	pF
R _g	Gate Resistance	f=1.0MHz	-	8	12	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{SD}	Forward On Voltage ²	I _S =-0.9A, V _{GS} =0V	-	-	-1.3	V
t _{rr}	Reverse Recovery Time	I _S =2A, V _{GS} =0V,	-	15	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	-	7	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse width ≤300us , duty cycle ≤2%.
- 3.Surface mounted on 1 in² copper pad of FR4 board, t≤5sec ; 180°C/W when mounted on min. copper pad.

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N-Channel

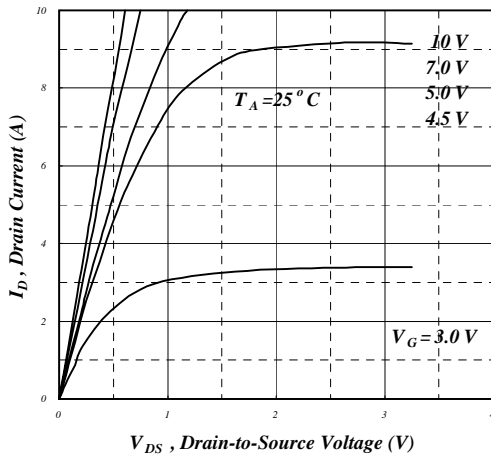


Fig 1. Typical Output Characteristics

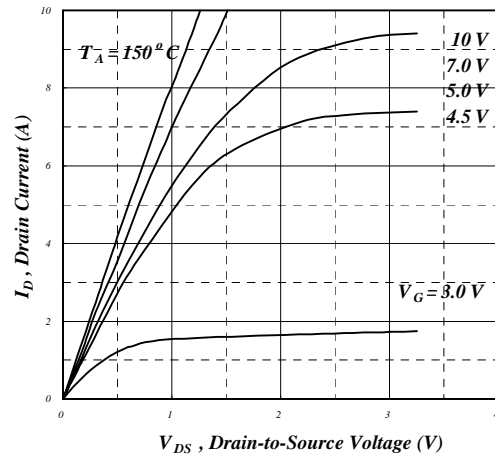


Fig 2. Typical Output Characteristics

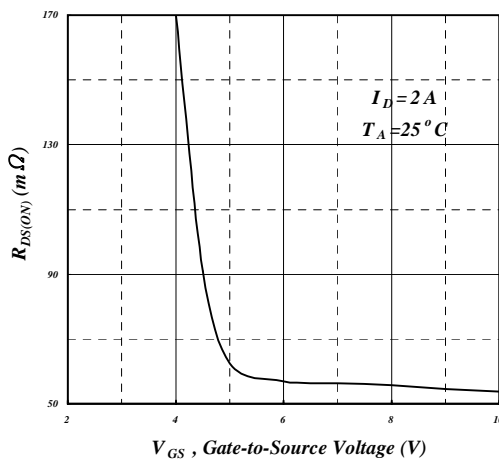


Fig 3. On-Resistance v.s. Gate Voltage

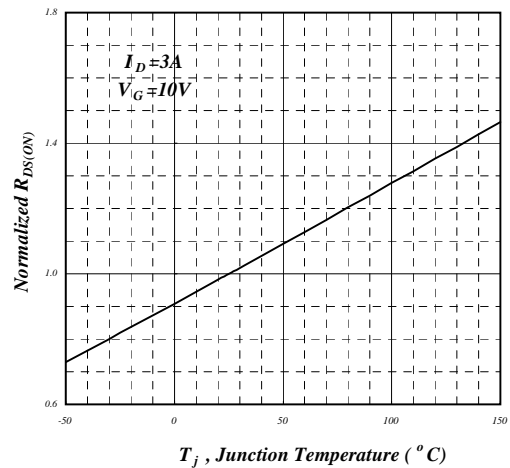


Fig 4. Normalized On-Resistance v.s. Junction Temperature

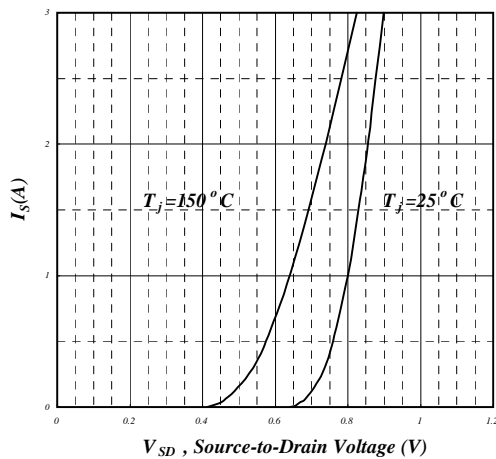


Fig 5. Forward Characteristic of Reverse Diode

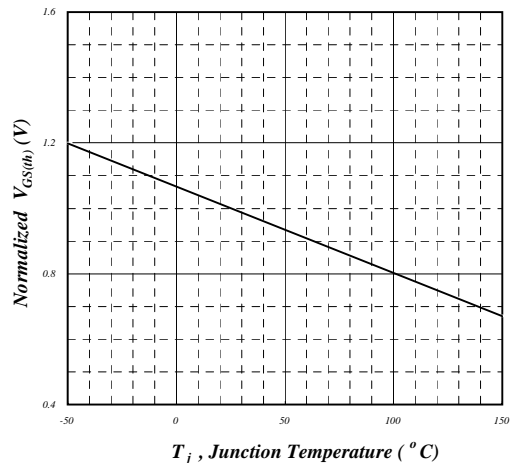


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



N-Channel

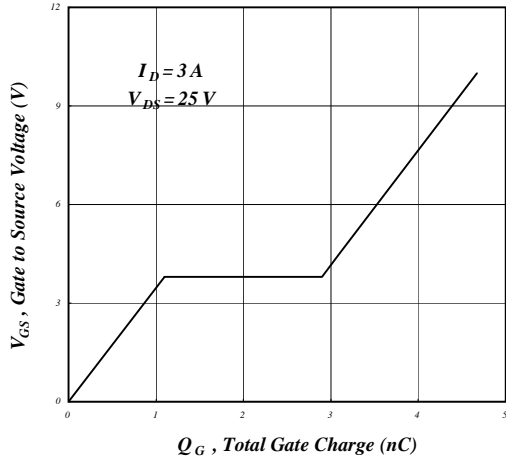


Fig 7. Gate Charge Characteristics

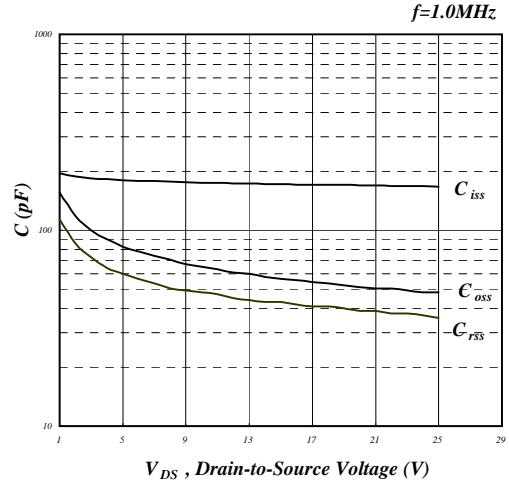


Fig 8. Typical Capacitance Characteristics

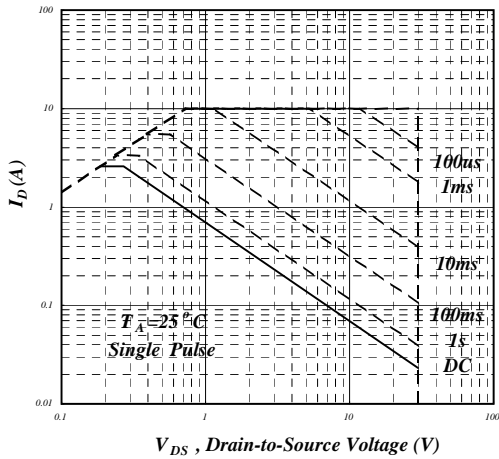


Fig 9. Maximum Safe Operating Area

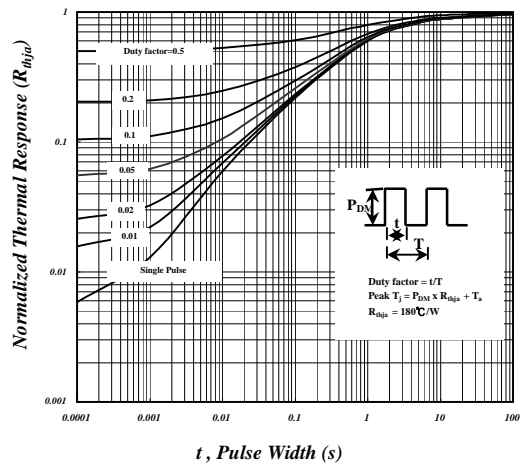


Fig 10. Effective Transient Thermal Impedance

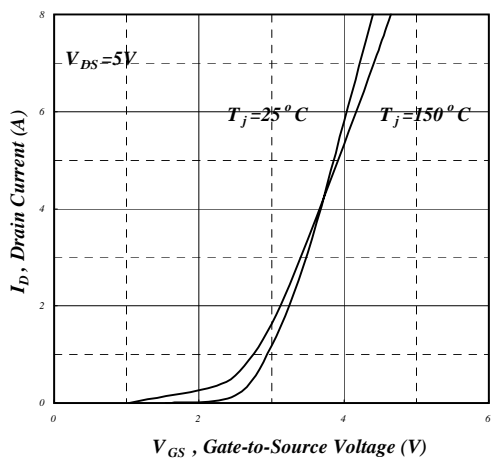


Fig 11. Transfer Characteristics

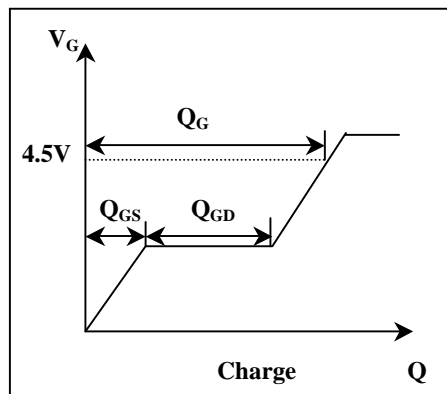


Fig 12. Gate Charge Waveform



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P-Channel

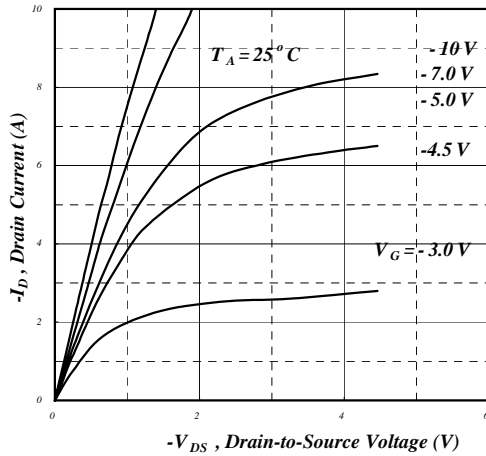


Fig 1. Typical Output Characteristics

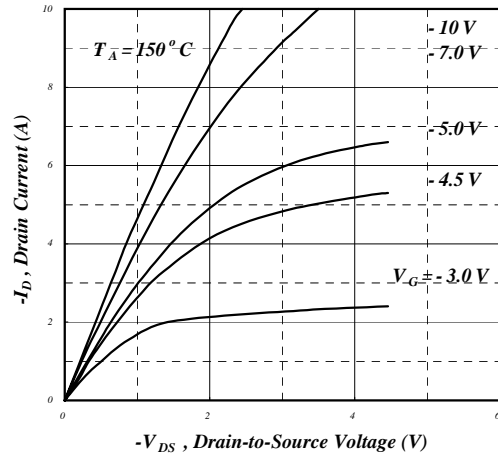


Fig 2. Typical Output Characteristics

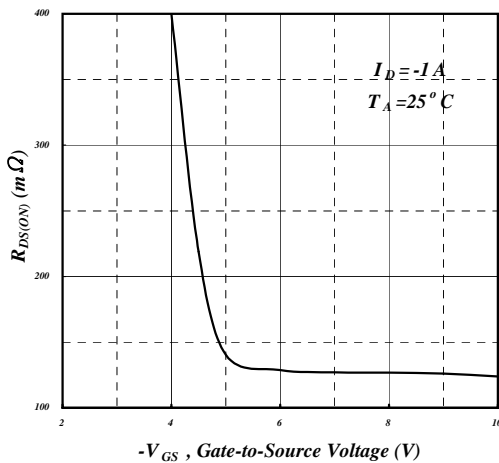


Fig 3. On-Resistance v.s. Gate Voltage

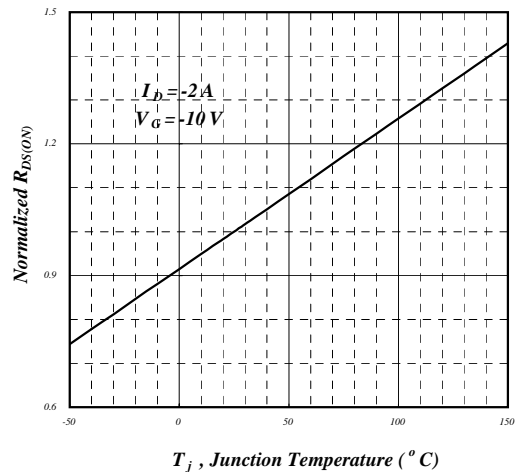


Fig 4. Normalized On-Resistance v.s. Junction Temperature

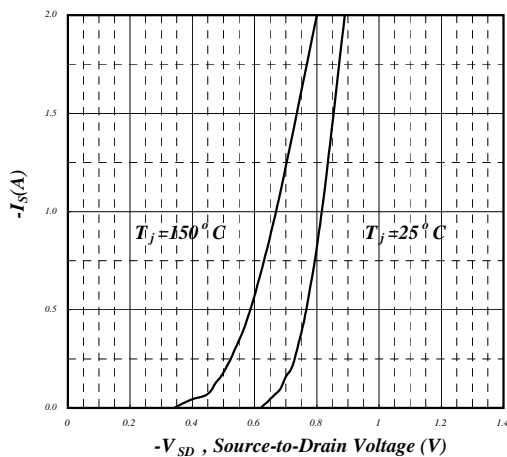


Fig 5. Forward Characteristic of Reverse Diode

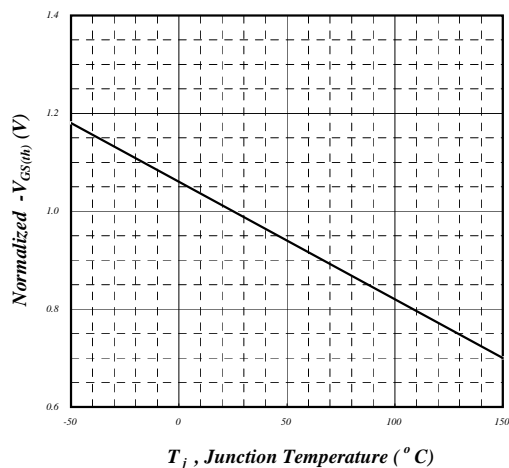


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



P-Channel

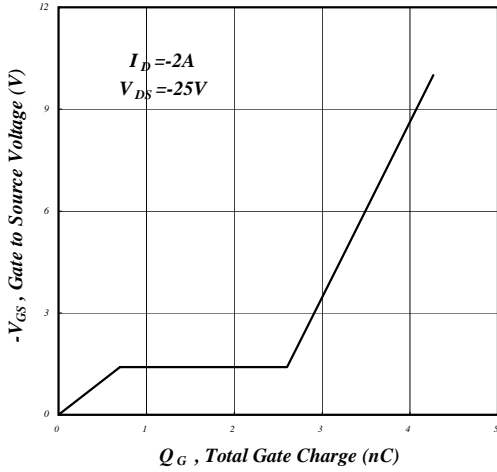


Fig 7. Gate Charge Characteristics

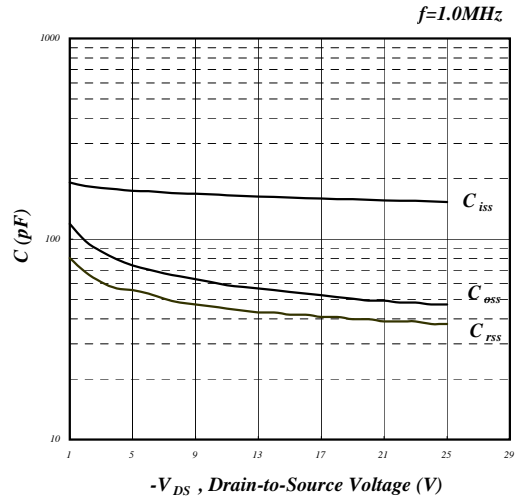


Fig 8. Typical Capacitance Characteristics

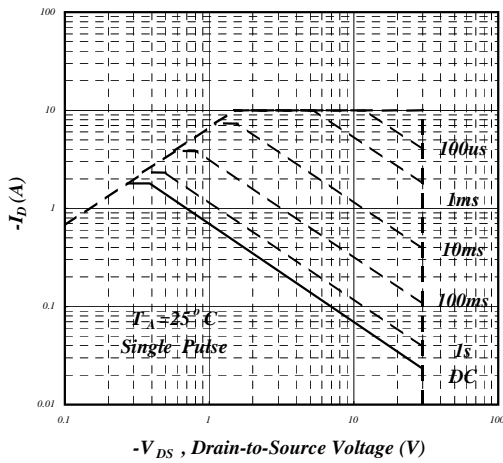


Fig 9. Maximum Safe Operating Area

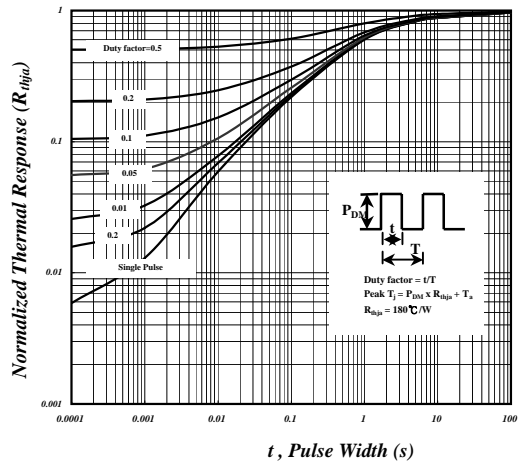


Fig 10. Effective Transient Thermal Impedance

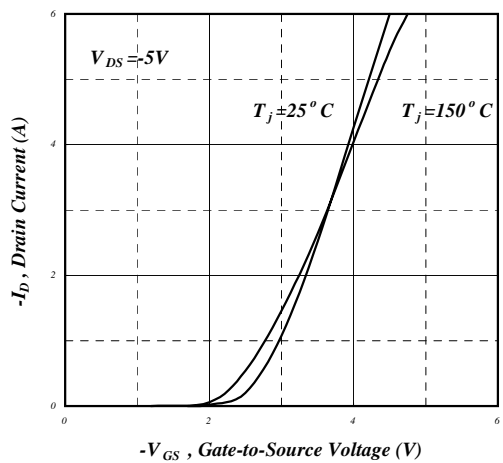


Fig 11. Transfer Characteristics

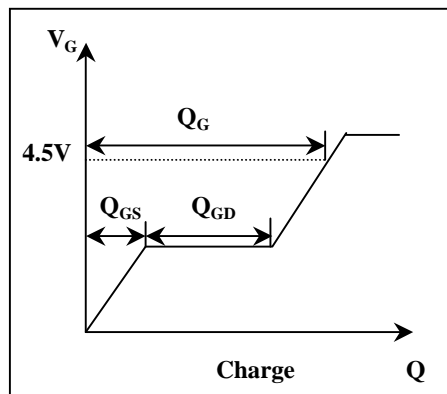


Fig 12. Gate Charge Waveform